

**AMENDMENTS TO THE CLAIMS**

**Claim 1 (Currently Amended):** A dry etching method for forming a resist film on a substrate comprising:

irradiating a substrate with a resist film formed thereon with radiation having a wavelength of not more than 195 nm to form a resist pattern having a minimum line width of not more than 200 nm,

subjecting the substrate having the resist pattern formed thereon to dry etching using, an etching gas perfluoro-2-pentyne, ~~or at least one kind of fluoropentene selected from 1,1,1,2,4,4,5,5,5-nonafluoro-2-pentene and 1,1,1,3,4,4,5,5,5-nonafluoro-2-pentene.~~

**Claim 2 (Original):** The dry etching method according to claim 1, wherein the resist film is formed from a high molecular weight compound containing 0% to 10% by weight of repeating units having an aromatic ring structure.

**Claims 3-5: (Cancelled).**

**Claim 6 (Previously Presented):** The dry etching method according to claim 1, wherein the dry etching is carried out under irradiation with plasma having a plasma density of at least  $10^{10}$  ions/cm<sup>3</sup>.

**Claim 7-12: (Cancelled).**